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Team Nexperia

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Rev. 10 — 8 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package	-			Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTC143EE	SOT416	SC-75	-	PDTA143EE	ultra small	
PDTC143EM	SOT883	SC-101	-	PDTA143EM	leadless ultra small	
PDTC143ET	SOT23	-	TO-236AB	PDTA143ET	small	
PDTC143EU	SOT323	SC-70	-	PDTA143EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
SOT23; S	OT323; SOT416		
1	input (base)	_	
2	GND (emitter)	3	
3	output (collector)	12	1 R1 R2 sym007
SOT883			
1	input (base)		
2	GND (emitter)		
3 output (collector)	output (collector)	2 Transparent top view	1 R1 R2 Sym007

3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
PDTC143EE	SC-75	plastic surface-mounted package; 3 leads	SOT416				
PDTC143EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883				
PDTC143ET	-	plastic surface-mounted package; 3 leads	SOT23				
PDTC143EU	SC-70	plastic surface-mounted package; 3 leads	SOT323				

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PDTC143EE	02
PDTC143EM	E1
PDTC143ET	*02
PDTC143EU	*02

[1] * = placeholder for manufacturing site code

PDTC143E_SER
Product data sheet

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

5. Limiting values

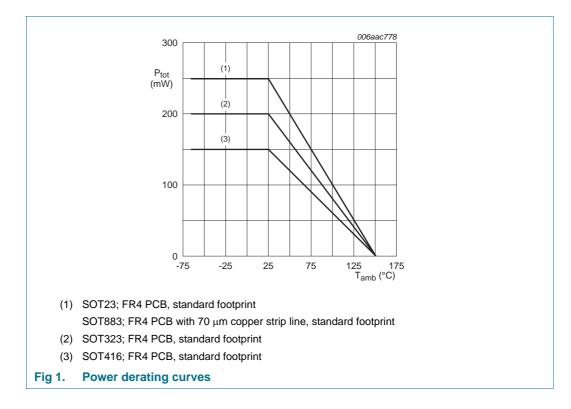
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+30	V
	negative		-	-10	V
I _O	output current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PDTC143EE (SOT416)		<u>[1][2]</u> _	150	mW
	PDTC143EM (SOT883)		[2][3]	250	mW
	PDTC143ET (SOT23)		<u>[1]</u> -	250	mW
	PDTC143EU (SOT323)		<u>[1]</u> -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70 µm copper strip line, standard footprint.

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω



6. Thermal characteristics

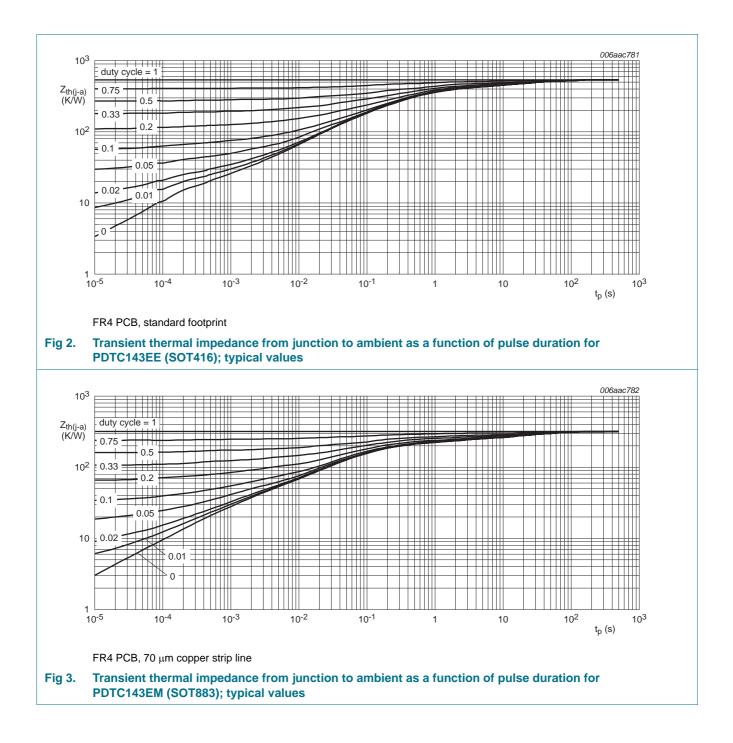
Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PDTC143EE (SOT416)		[1][2]	-	830	K/W
	PDTC143EM (SOT883)		[2][3]	-	500	K/W
	PDTC143ET (SOT23)		<u>[1]</u> -	-	500	K/W
	PDTC143EU (SOT323)		<u>[1]</u> -	-	625	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

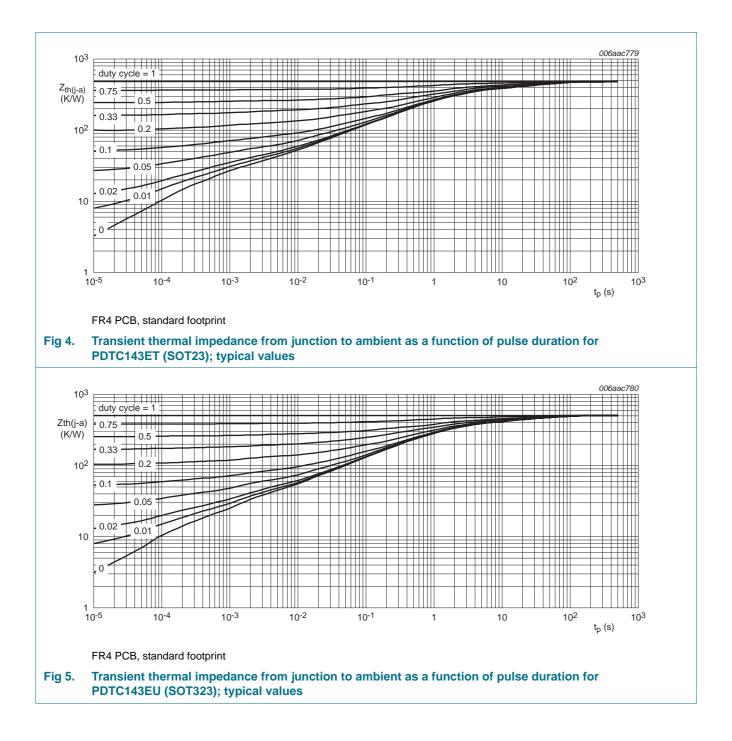
[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70 μ m copper strip line, standard footprint.

PDTC143E series



PDTC143E series



NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

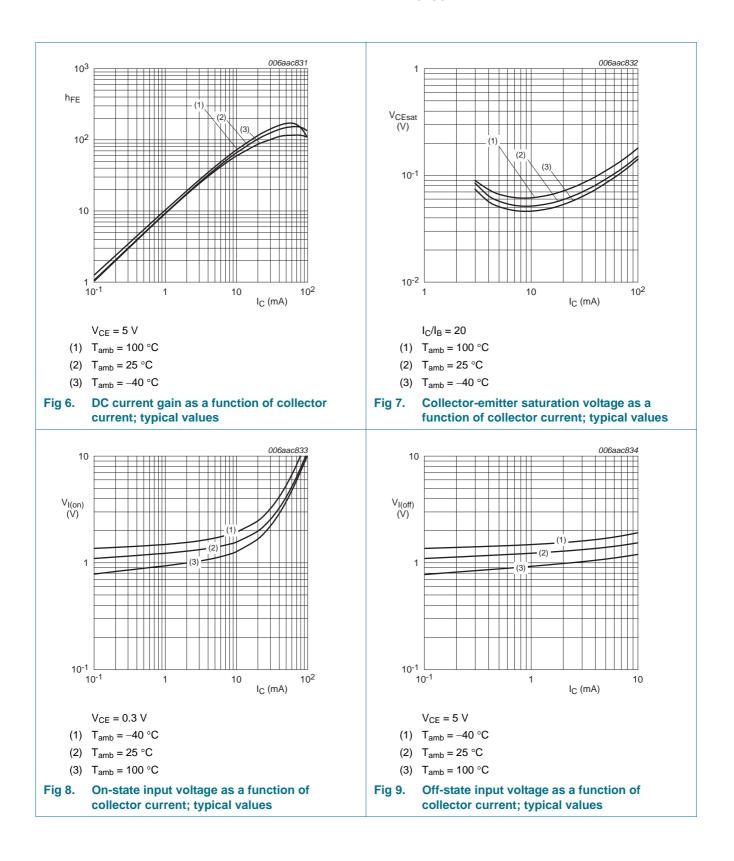
7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$		-	-	1	μA
	cut-off current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	900	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$		30	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 10 mA; I_{B} = 0.5 mA		-	-	150	mV
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μ A		-	1.1	0.5	V
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I _C = 20 mA		2.5	1.9	-	V
R1	bias resistor 1 (input)			3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	-	2.5	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	<u>[1]</u>	-	230	-	MHz

[1] Characteristics of built-in transistor

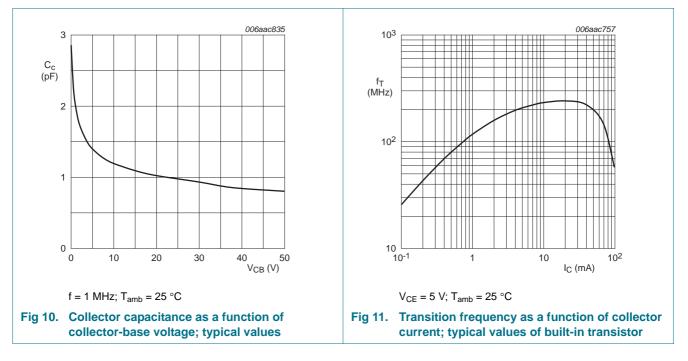
PDTC143E_SER
Product data sheet

PDTC143E series



PDTC143E series

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω



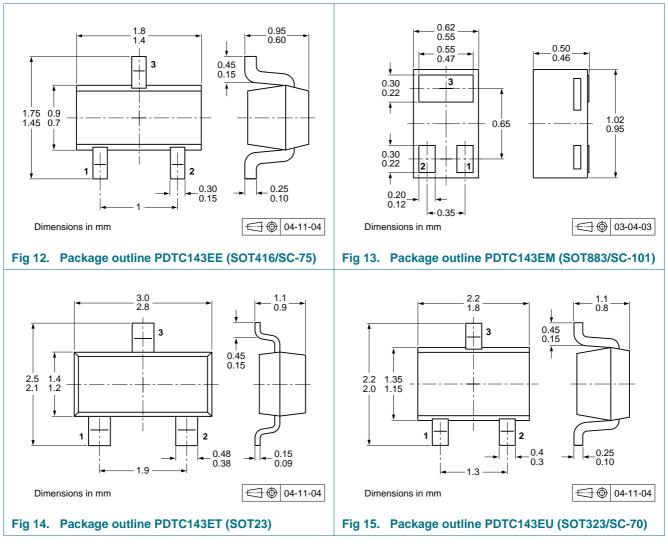
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

9. Package outline



10. Packing information

Table 9.Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

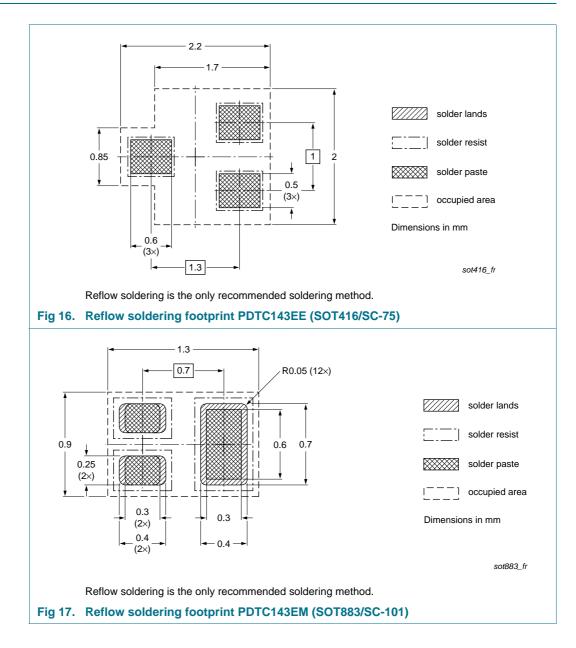
Type number	Package	Description	Packing	Packing quantity		
			3000	5000	10000	
PDTC143EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC143EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315	
PDTC143ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTC143EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

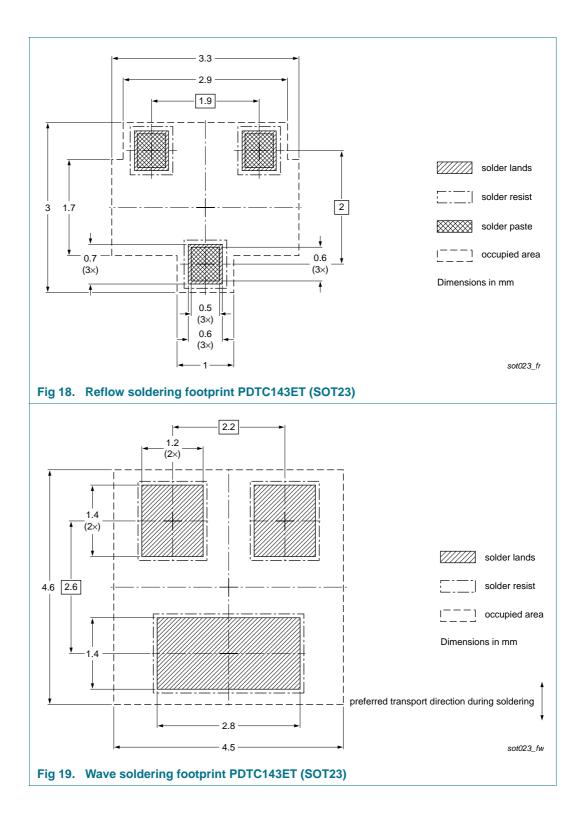
[1] For further information and the availability of packing methods, see Section 14.

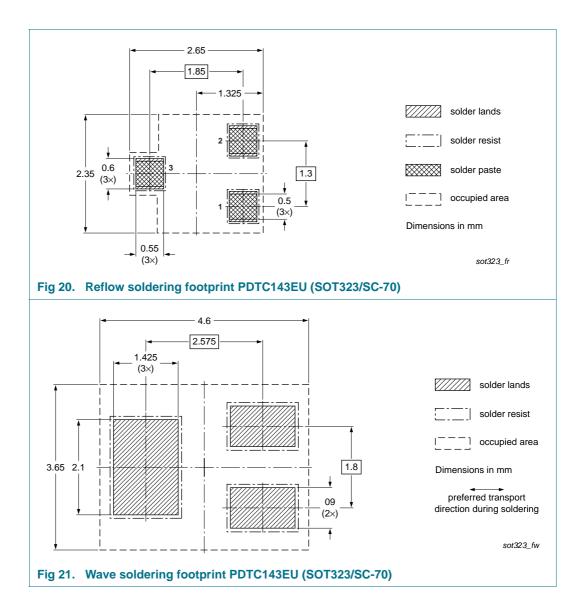
PDTC143E_SER Product data sheet

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

11. Soldering







NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTC143E_SER v.10	20111208	Product data sheet	-	PDTC143E_SERIES v.9			
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 						
	 Legal texts have been adapted to the new company name where appropriate. 						
	 Type numbers PDTC143EEF, PDTC143EK and PDTC143ES removed. 						
	 Section 1 "F 	Product profile": updated					
	 <u>Section 4 "Marking"</u>: updated 						
	• Figure 1 to 11: added						
	 <u>Section 6 "Thermal characteristics"</u>: updated 						
		<u>aracteristics"</u> : V _{i(on)} redefine te input voltage, I _{CEO} update		t voltage, V _{i(off)} redefined t			
	<u>Section 8 "Test information"</u> : added						
	 <u>Section 9 "Package outline"</u>: superseded by minimized package outline drawings 						
	<u>Section 10 "Packing information"</u> : added						
	<u>Section 11 "Soldering</u> ": added						
	 Section 13 ' 	<u>'Legal information</u> ": updated					
PDTC143E_SERIES v.9	20040805	Product data sheet	-	PDTC143E_SERIES v.8			
PDTC143E_SERIES v.8	20040318	Product specification	-	PDTC143E_SERIES v.			
PDTC143E_SERIES v.7	20040112	Product specification	-	PDTC143E_SERIES v.6			
PDTC143E_SERIES v.6	20030910	Product specification	-	PDTC143E_SERIES v.			
PDTC143E SERIES v.5	20030410	Product specification	-	_			

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PDTC143E_SER

Product data sheet

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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PDTC143E series

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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